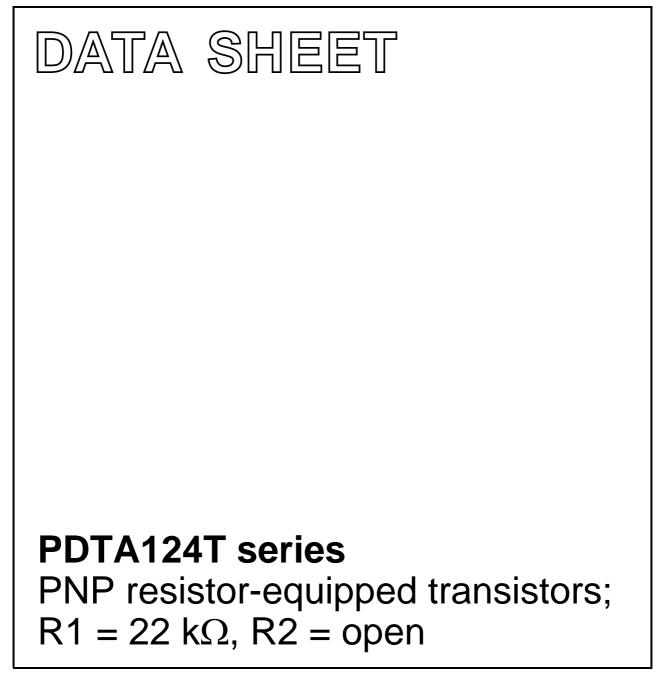
DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 2004 May 05 2004 Aug 04



#### **PDTA124T series**

#### FEATURES

- · Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

#### APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

**PRODUCT OVERVIEW** 

#### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	-	-50	V
lo	output current (DC)	-	-100	mA
R1	bias resistor	22	-	kΩ
R2	open	-	-	-

#### DESCRIPTION

PNP resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

TYPE NUMBER	PACKAGE		MARKING CODE	NPN COMPLEMENT	
ITPE NUMBER	PHILIPS	EIAJ	MARKING CODE	NPN COMPLEMENT	
PDTA124TE	SOT416	SC-75	3R	PDTC124TE	
PDTA124TEF	SOT490	SC-89	24	PDTC124TEF	
PDTA124TK	SOT346	SC-59	59	PDTC124TK	
PDTA124TM	SOT883	SC-101	DJ	PDTC124TM	
PDTA124TS	SOT54 (TO-92)	SC-43	TA124T	PDTC124TS	
PDTA124TT	SOT23	_	*AE <sup>(1)</sup>	PDTC124TT	
PDTA124TU	SOT323	SC-70	*7B <sup>(1)</sup>	PDTC124TU	

#### Note

- 1. \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.
  - \* = W: Made in China.

# PNP resistor-equipped transistors; $R1 = 22 \text{ k}\Omega$ , R2 = open

# PDTA124T series

#### SIMPLIFIED OUTLINE, SYMBOL AND PINNING

	SIMPLIFIED OUTLINE AND SYMBOL		PINNING		
TYPE NUMBER	SER SIMPLIFIED OUTLINE AND STMBOL		DESCRIPTION		
PDTA124TS		PIN           1           2           3	DESCRIPTION base collector emitter		
PDTA124TE PDTA124TEF PDTA124TK PDTA124TT PDTA124TU	$\begin{array}{c} \hline 3 \\ \hline 1 \\ \hline \end{array} \\ Top view \end{array}$	1 2 3	base emitter collector		
PDTA124TM	2 1 Bottom view MDB266	1 2 3	base emitter collector		

### PDTA124T series

#### **ORDERING INFORMATION**

TYPE	PACKAGE				
NUMBER	NAME	DESCRIPTION	VERSION		
PDTA124TE	_	plastic surface mounted package; 3 leads	SOT416		
PDTA124TEF	_	<ul> <li>plastic surface mounted package; 3 leads</li> <li>SOT490</li> </ul>			
PDTA124TK	_	plastic surface mounted package; 3 leads SOT3			
PDTA124TM	_	leadless ultra small plastic package; 3 solder lands; body $1.0 \times 0.6 \times 0.5$ mm			
PDTA124TS	_	<ul> <li>plastic single-ended leaded (through hole) package; 3 leads</li> <li>SOT</li> </ul>			
PDTA124TT	-	<ul> <li>plastic surface mounted package; 3 leads</li> <li>SOT23</li> </ul>			
PDTA124TU	<ul> <li>plastic surface mounted package; 3 leads</li> <li>SOT323</li> </ul>		SOT323		

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	-5	V
lo	output current (DC)		-	-100	mA
I <sub>CM</sub>	peak collector current		-	-100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT23	note 1	-	250	mW
	SOT54	note 1	-	500	mW
	SOT323	note 1	-	200	mW
	SOT346	note 1	-	250	mW
	SOT416	note 1	_	150	mW
	SOT490	notes 1 and 2	-	250	mW
	SOT883	notes 2 and 3	-	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu m$  copper strip line.

### PDTA124T series

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air		
	SOT23	note 1	500	K/W
	SOT54	note 1	250	K/W
	SOT323	note 1	625	K/W
	SOT346	note 1	500	K/W
	SOT416	note 1	833	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

#### Notes

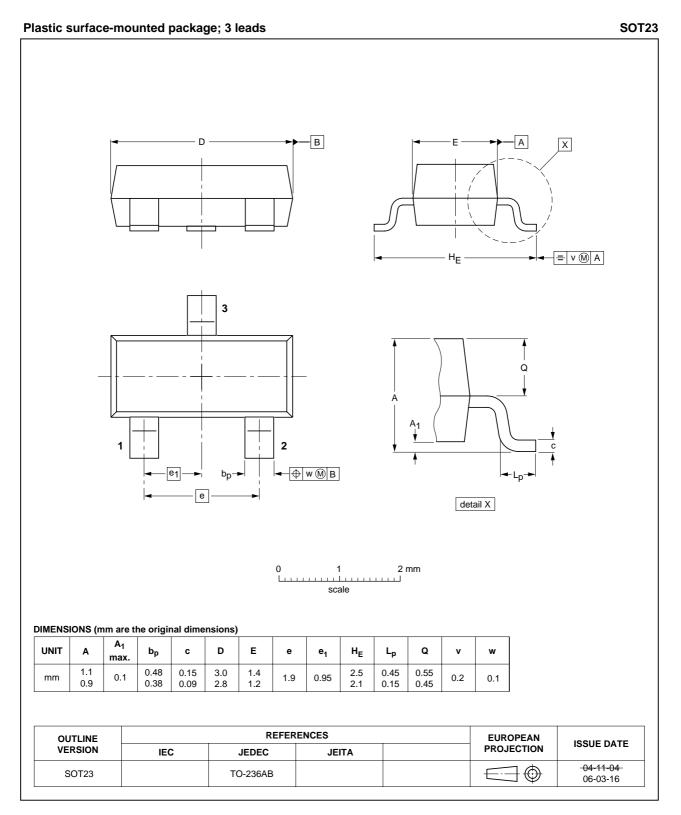
- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

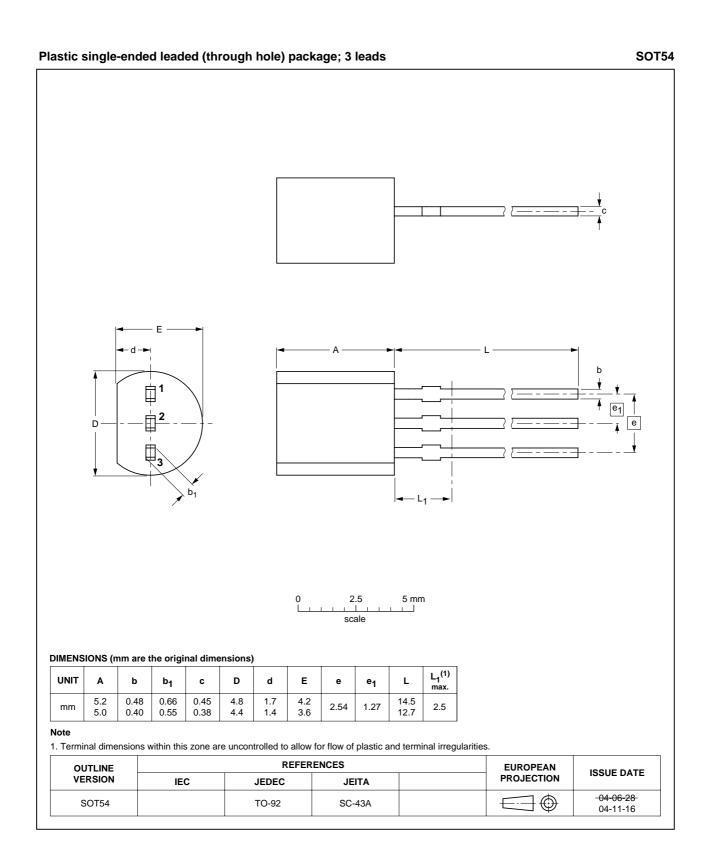
#### CHARACTERISTICS

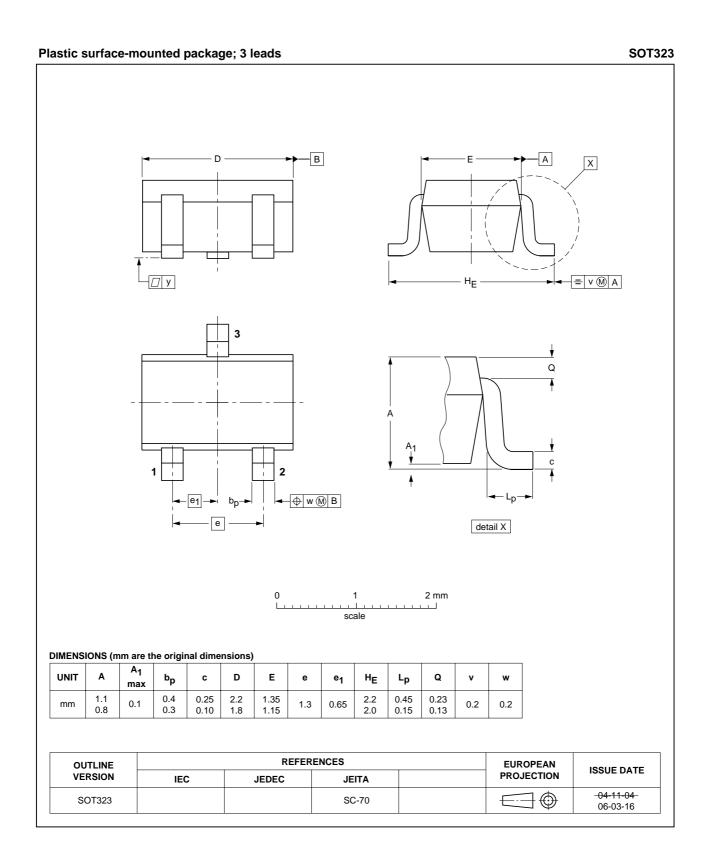
 $T_{amb}$  = 25 °C unless otherwise specified.

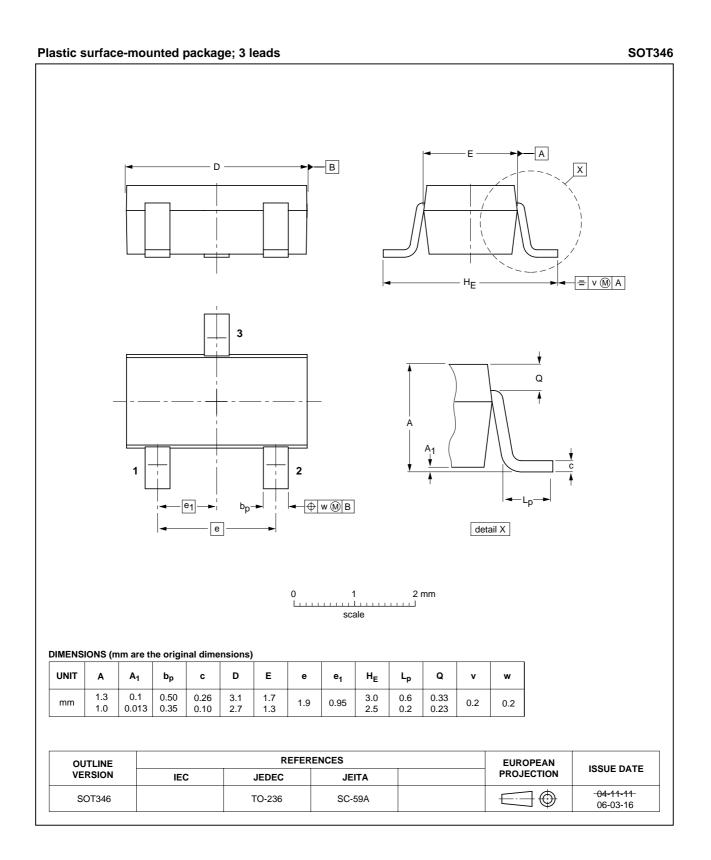
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	_	_	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; \text{ I}_{B} = 0 \text{ A}$	_	_	-1	μA
		$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A};$ T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	_	_	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -1 \text{ mA}$	100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{\rm C} = -10 \text{ mA}; I_{\rm B} = -0.5 \text{ mA}$	-	-	-150	mV
R1	input resistor		15.4	22	28.6	kΩ
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0 A; V_{CB} = -10 V;$ f = 1 MHz	-	-	3	pF

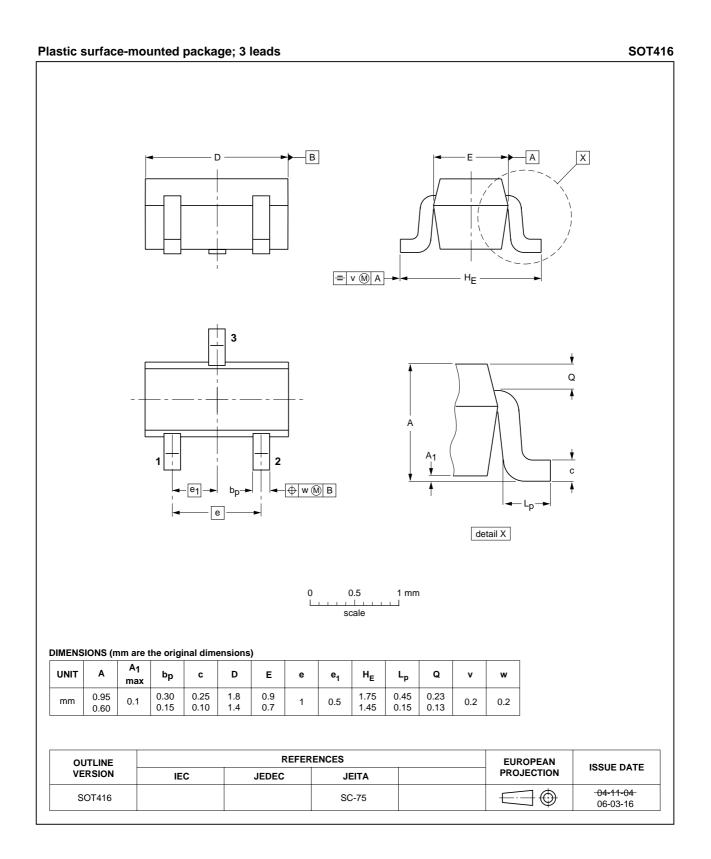
#### PACKAGE OUTLINES

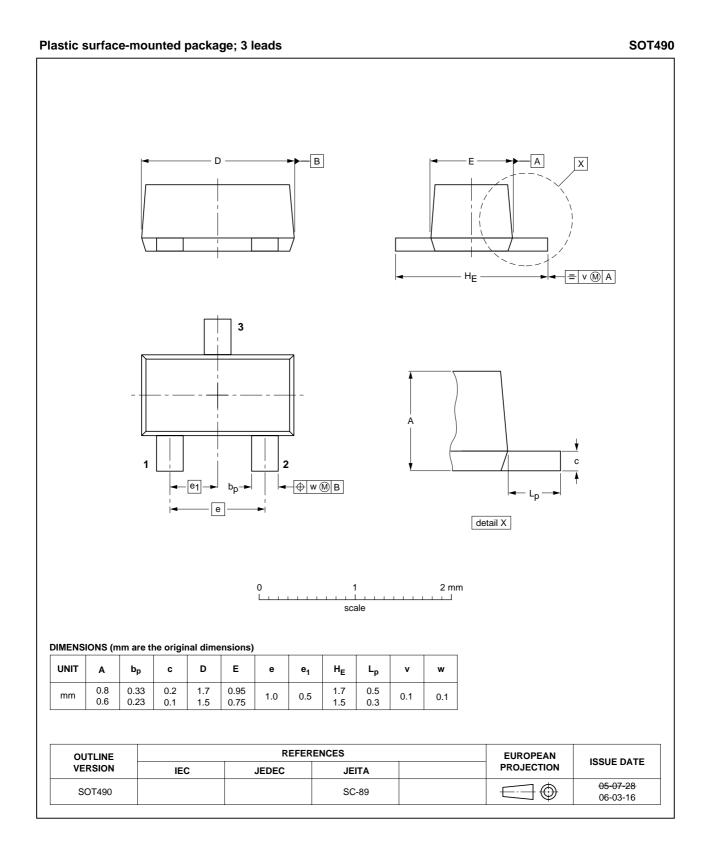


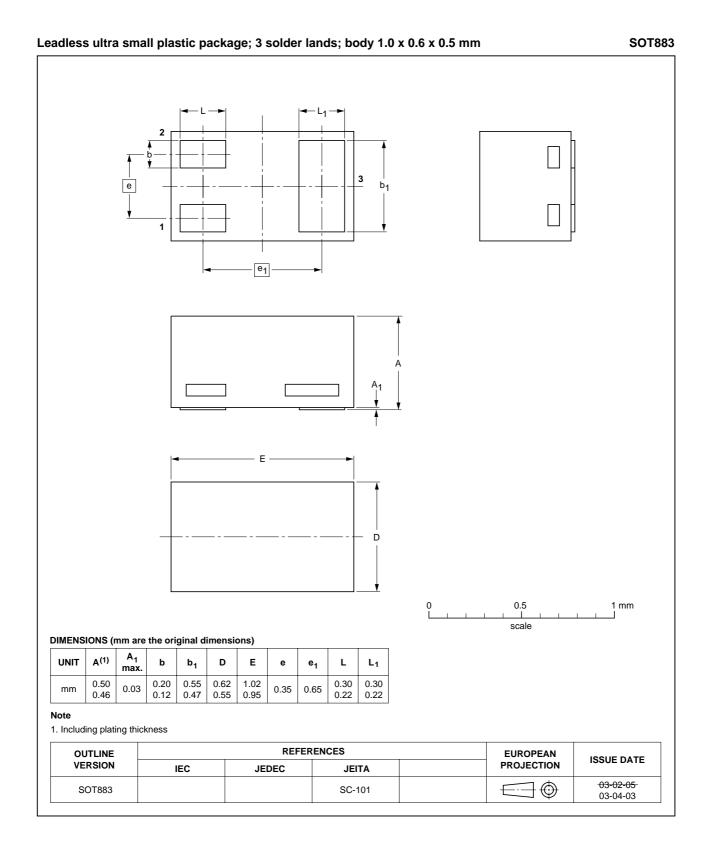












#### PDTA124T series

#### DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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# **NXP Semiconductors**

#### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

#### **Contact information**

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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Printed in The Netherlands

R75/03/pp14

Date of release: 2004 Aug 04

Document order number: 9397 750 13653

